



**Thyristor Module**

**Features**

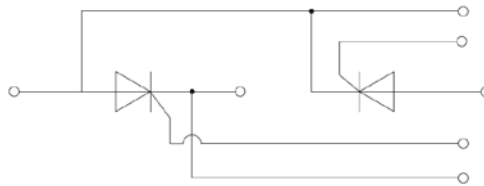
- Half-bridge SCR configuration integrated in a single package
- With high thermal conductivity DBC as the Insulation
- Welding by vacuum welding technology, which provide high reliability

**Product Summary**

Parameter	Value	Unit
$V_{RRM}$	1800	V
$I_{T(AV)}$ (@ $T_C = 85^\circ C$ )	250	A
$I_{TSM}$ (@ $t_p = 10ms$ )	8300	A
$V_T(Max)$	1.80	V

**Applications**

- Temperature control
- Light control system
- DC motor



**Absolute Maximum Ratings (@  $T_C = 25^\circ C$  unless otherwise specified)**

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak off-state voltage	$T_{vj} = 25^\circ C$	$V_{DRM}$	1800	V
Repetitive peak reverse voltage	$T_{vj} = 25^\circ C$	$V_{RRM}$	1800	V
Non-repetitive peak off-state voltage	$T_{vj} = 25^\circ C$	$V_{DSM}$	1900	V
Non-repetitive peak reverse voltage	$T_{vj} = 25^\circ C$	$V_{RSM}$	1900	V
Average forward current	$T_C = 85^\circ C$	$I_{T(AV)}$	250	A
Forward surge current	$t_p=10ms V_R=0.6V_{RRM}$	$I_{TSM}$	8300	A
$I^2t$ value for fusing		$I^2t$	344450	$A^2s$
Critical rate of rise of on-state current	$I_G=2 \times I_{GT}$	$di/dt$	150	$A/\mu s$
RMS isolation voltage	A.C 50Hz(1s/1min)	$V_{ISO}$	3600/3000	V
Junction temperature range		$T_J$	-40 ~ +125	$^\circ C$
Storage temperature range		$T_{stg}$	-40 ~ +125	$^\circ C$

**Electrical Characteristics (@  $T_c = 25^\circ\text{C}$  unless otherwise specified)**

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Peak forward voltage	$I_T=750\text{A}$ , $t_P=380\mu\text{s}$	$V_T$			1.80	V
Repetitive peak off-state current	$V_D = V_{\text{DRM}}$ , $T_c = 25^\circ\text{C}$	$I_{\text{DRM}}$			100	$\mu\text{A}$
	$V_D = V_{\text{DRM}}$ , $T_c = 125^\circ\text{C}$				100	mA
Reverse leakage current	$V_R = V_{\text{RRM}}$ , $T_c = 25^\circ\text{C}$	$I_{\text{RRM}}$			100	$\mu\text{A}$
	$V_R = V_{\text{RRM}}$ , $T_c = 125^\circ\text{C}$				100	mA
Threshold voltage	For power loss calculation only $T_{vj} = 125^\circ\text{C}$ ,	$V_{\text{TO}}$			0.8	V
Dynamic resistance	$T_{vj} = 125^\circ\text{C}$ ,	$r_T$			1.05	$\text{m}\Omega$
Triggering gate current	$V_D=12\text{V}$ $R_L=30\Omega$	$I_{\text{GT}}$	20		150	mA
Holding current	$I_T=1\text{A}$	$I_H$			300	mA
Latching current	$I_G=1.2 I_{\text{GT}}$	$I_L$			400	mA
Triggering gate voltage	$V_D=12\text{V}$ $R_L=30\Omega$	$V_{\text{GT}}$			1.8	V
Non triggering gate voltage	$V_D=0.5V_{\text{DRM}}$ $T_{vj}=125^\circ\text{C}$	$V_{\text{GD}}$			0.25	V

**Thermal Characteristics (@  $T_c = 25^\circ\text{C}$  unless otherwise specified)**

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	per Thyristor	$R_{\text{th(j-c)}}$		0.11		$^\circ\text{C}/\text{W}$
Thermal resistance, case to heatsink	per Thyristor	$R_{\text{th(c-s)}}$		0.06		$^\circ\text{C}/\text{W}$
Mounting torque	Module and heatsink fixed torque M5	M	4.25		5.75	N·m
	Electrode connection torque M8		7.65		10.35	N·m



Ordering Information

Device	Marking	Package	Weight	Inner Box	Pre Carton
JMT250KT18T3	JMT250KT18T3	T3	355±10g/PCS	3 PCS	27 PCS

Typical Electrical & Thermal Characteristics

FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

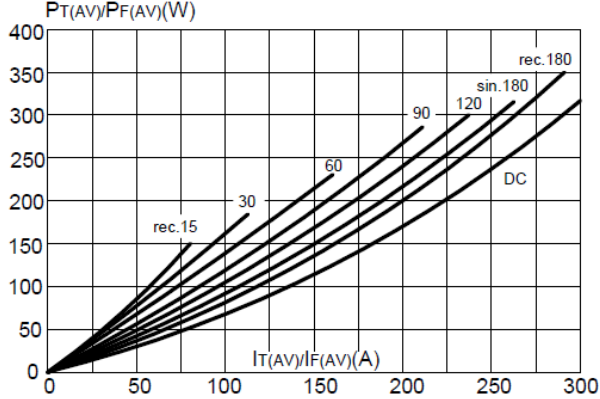


FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

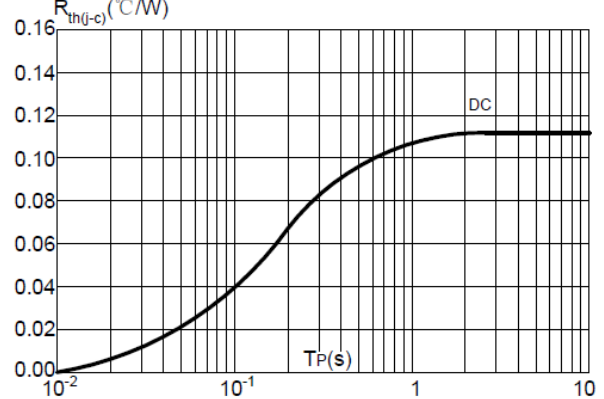


FIG.3: Forward characteristics (per thyristor or diode)

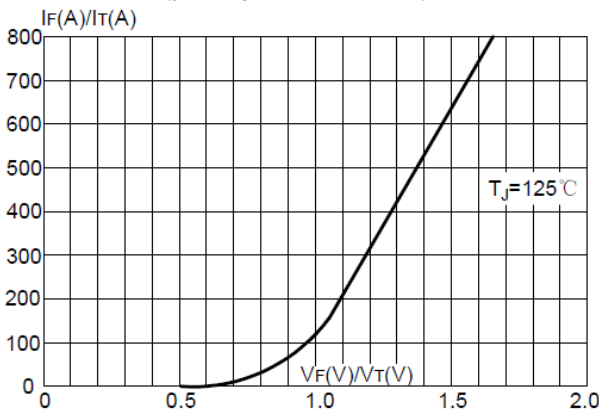
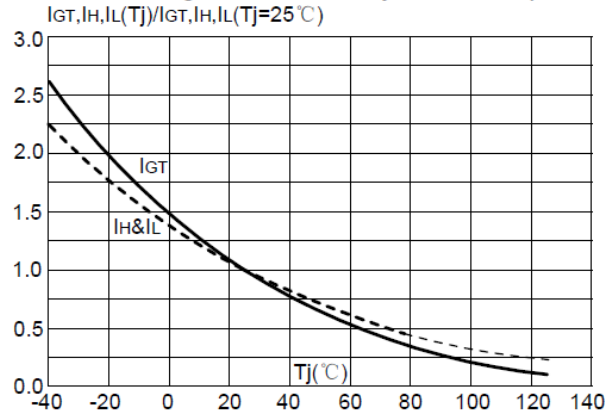
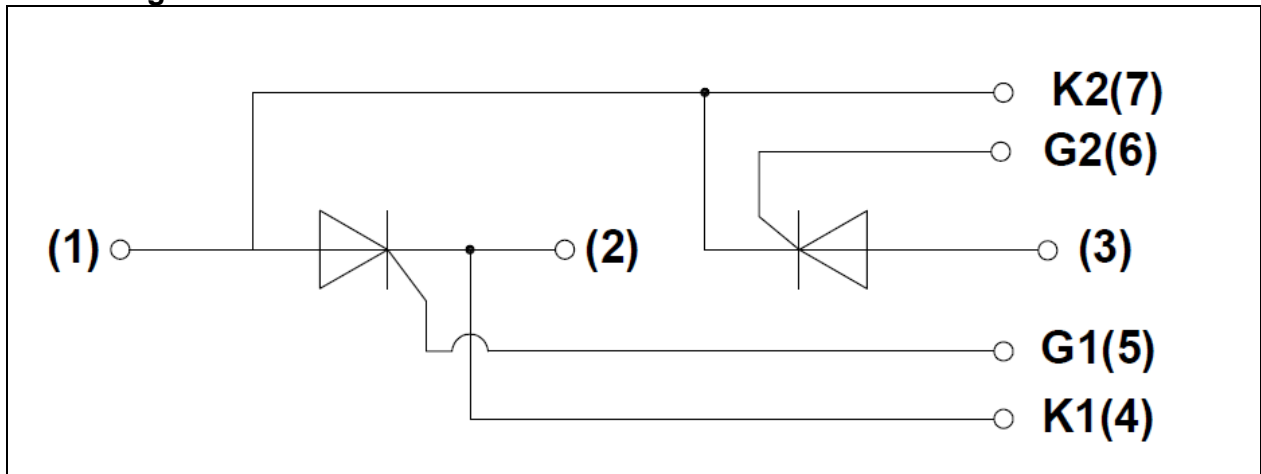


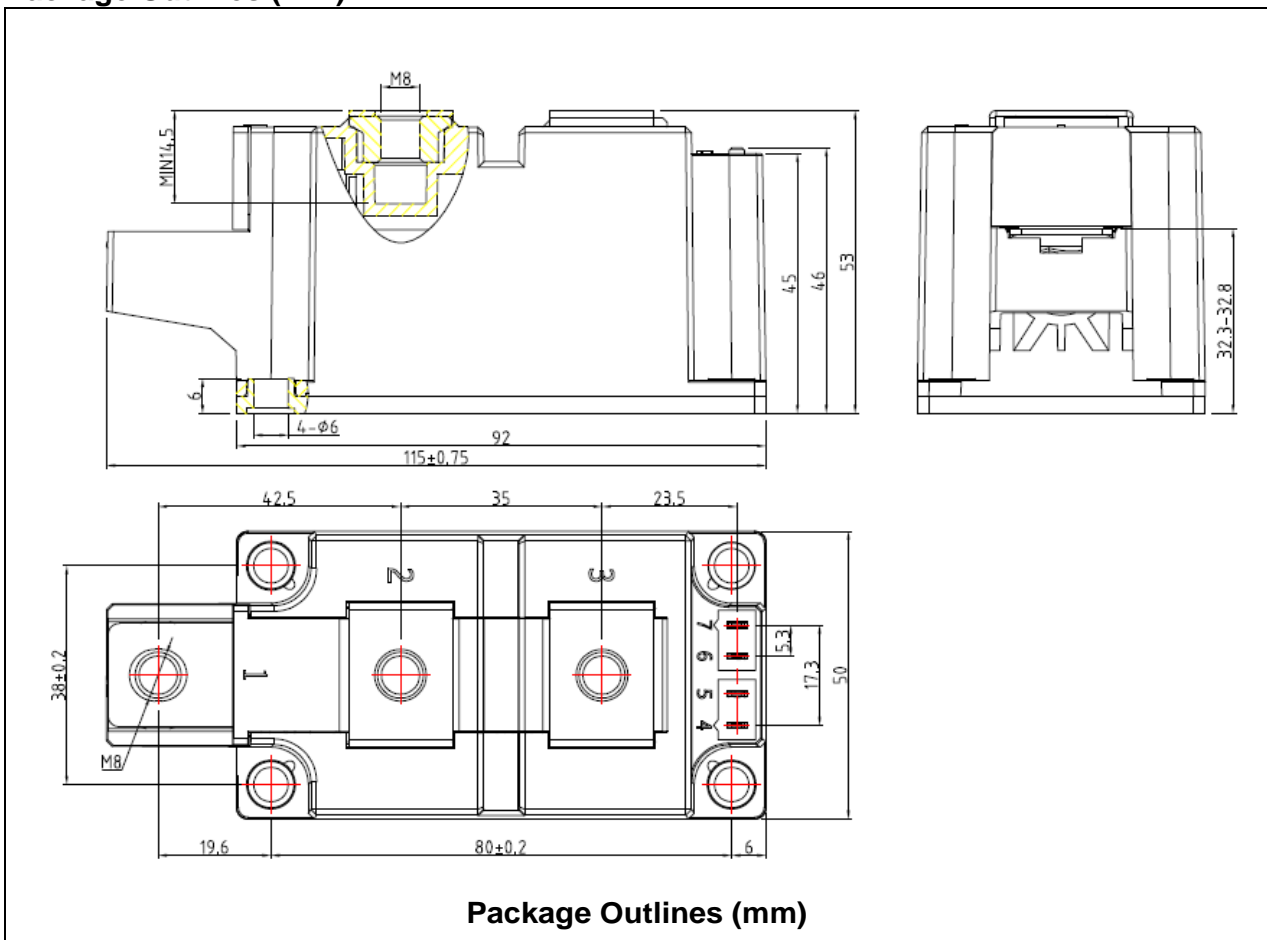
FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature



**Circuit Diagram**




**Package Outlines (mm)**





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